TOSHIBA Field Effect Transistor Silicon P Channel MOS Type

# **2SJ200**

## **High Power Amplifier Application**

Unit: mm

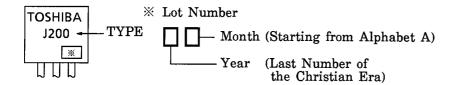
 $\begin{array}{ll} \bullet & \mbox{High breakdown voltage} & : V_{DSS} = -180 \ V \\ \bullet & \mbox{High forward transfer admittance} & : |Y_{fs}| = 4.0 \ S \ (\mbox{typ.}) \end{array}$ 

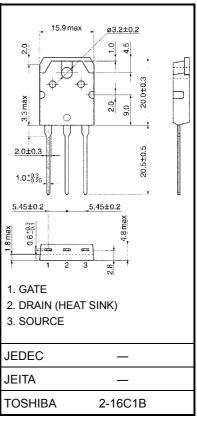
• Complementary to 2SK1529

## **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit	
Drain-source voltage	$V_{DSS}$	-180	V	
Gate-source voltage	$V_{GSS}$	±20	V	
Drain current (Note 1)	I <sub>D</sub>	-10	Α	
Drain power dissipation (Tc = 25°C)	$P_{D}$	120	W	
Channel temperature	T <sub>ch</sub>	150	°C	
Storage temperature range	T <sub>stg</sub>	-55~150	°C	

## Marking





Weight: 4.6 g (typ.)

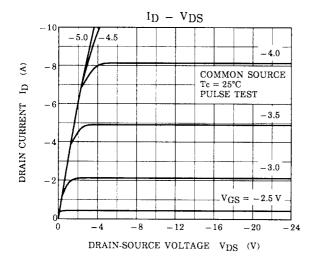
## **Electrical Characteristics (Ta = 25°C)**

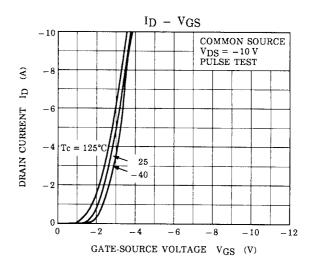
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = -180 V, V <sub>GS</sub> = 0	_	_	-1.0	mA
Gate leakage current	I <sub>GSS</sub>	V <sub>DS</sub> = 0, V <sub>GS</sub> = ±20 V	_	_	±0.5	μΑ
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	$I_D = -10 \text{ mA}, V_{GS} = 0$	-180	_	_	٧
Gate-source cut-off voltage (Note 2)	V <sub>GS (OFF)</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -0.1 A	-0.8	_	-2.8	٧
Drain-source saturation voltage	V <sub>DS (ON)</sub>	$I_D = -6 \text{ A}, V_{GS} = -10 \text{ V}$	_	-1.5	-5.0	V
Forward transfer admittance	Y <sub>fs</sub>	$V_{DS} = -10 \text{ V}, I_D = -3 \text{ A}$	_	4.0	_	S
Input capacitance	C <sub>iss</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	1300	_	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0, f = 1 MHz	_	350	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0, f = 1 MHz	_	200	_	

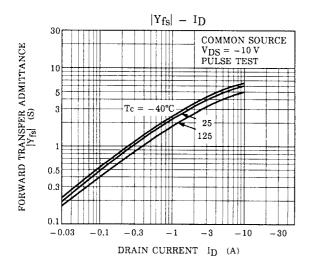
Note 1: Please use devices on condition that the channel temperature is below 150°C.

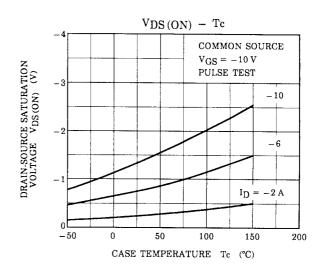
Note 2: V<sub>GS (OFF)</sub> Classification O: -0.8~-1.6, Y: -1.4~-2.8

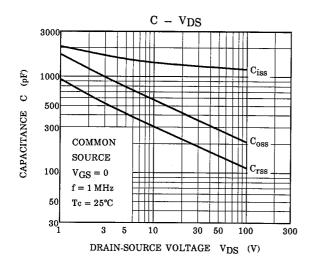
This transistor is an electrostatic sensitive device. Please handle with caution.

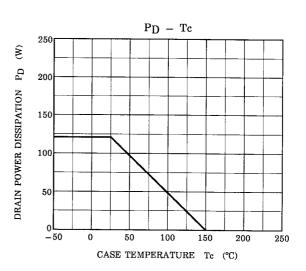




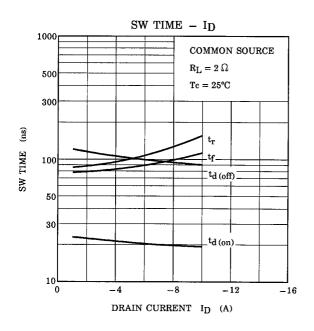


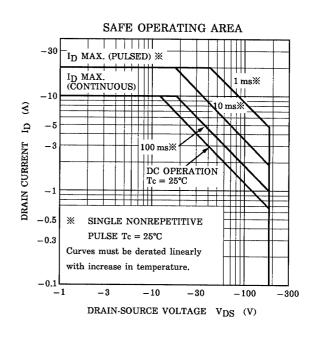




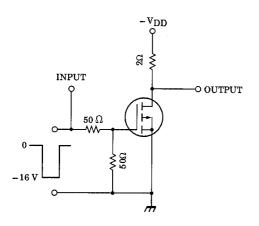


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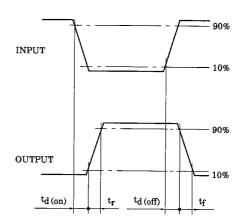


## **Switching Time Test Circuit**



### **Waveforms**

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